Jiro Matsuo

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

272 papers	4,650 citations	36 h-index	55 g-index
307 ext. papers	4,929 ext. citations	2.4 avg, IF	5.12 L-index

#	Paper	IF	Citations
272	Innovative Technologies in Advanced SIMS： Toward Organic and Biological Material Analysis. *Vacuum and Surface Science*, **2021**, 64, 458-465	0	
271	Photoinduced oxygen transport in cobalt double-perovskite crystal EuBaCo2O5.39. *Applied Materials Today*, **2021**, 24, 101167	6.6	2
270	Secondary ion mass spectrometry measurements under ambient and humid conditions using MeV ions. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2020**, 38, 034014	1.3	2
269	Phonon transport probed at carbon nanotube yarn/sheet boundaries by ultrafast structural dynamics. *Carbon*, **2020**, 170, 165-173	10.4	3
268	Optimized Alkali-Metal Cationization in Secondary Ion Mass Spectrometry of Polyethylene Glycol Oligomers with up to / 10000: Dependence on Cation Species and Concentration. *Analytical Chemistry*, **2020**, 92, 1511-1517	7.8	0
267	MeV-SIMS measurement of lithium-containing electrolyte. *Nuclear Instruments & Methods in Physics Research B*, **2020**, 479, 229-232	1.2	1
266	Selective Reduction Mechanism of Graphene Oxide Driven by the Photon Mode the Thermal Mode. *ACS Nano*, **2019**, 13, 10103-10112	16.7	21
265	Cluster ion beam bombardment and Q-ToF-SIMS analysis of large biomolecules. *Nuclear Instruments & Methods in Physics Research B*, **2019**, 448, 11-18	1.2	1
264	Gas cooling secondary ions emitted by gas cluster ion beam at the travelling-wave ion guide of a Q-ToF-SIMS system. *Nuclear Instruments & Methods in Physics Research B*, **2019**, 450, 139-143	1.2	1
263	In situ cationization of molecular ions sputtered from organic specimens under cluster bombardment. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2018**, 36, 03F106	1.3	1
262	Recent Progress of SIMS Technique： from Novel Primary Beams to Advanced Mass Spectrometers. *Vacuum and Surface Science*, **2018**, 61, 426-434	0	1
261	Observation of Adsorption and Desorption of Water Molecules with Ambient SIMS. *Microscopy and Microanalysis*, **2018**, 24, 334-335	0.5	
260	Cationization and fragmentation of molecular ions sputtered from polyethylene glycol under gas cluster bombardment: An analysis by MS and MS/MS. *International Journal of Mass Spectrometry*, **2018**, 430, 149-157	1.9	4
259	Fabrication of a Si lever structure made by double-angled etching with reactive gas cluster injection. *Applied Physics Letters*, **2017**, 110, 182105	3.4	0
258	Angled etching of Si by ClF3／Ar gas cluster injection. *Japanese Journal of Applied Physics*, **2017**, 56, 06HB02	1.4	4
257	Molecular imaging of alkaloids in khat (Catha edulis) leaves with MeV-SIMS. *Nuclear Instruments & Methods in Physics Research B*, **2017**, 404, 140-145	1.2	5
256	Observation of Liquid Water with Ambient SIMS. *Transactions of the Materials Research Society of Japan*, **2016**, 41, 309-311	0.2	

255	Recent Developments of Cluster Ion Beam —From Nano-fabrication to Analysis of Bio-materials—. *Journal of the Vacuum Society of Japan*, **2016**, 59, 113-120		
254	Recent Progress in Cluster Beam Technique. *Journal of the Japan Society for Precision Engineering*, **2016**, 82, 309-314	0.1	0
253	Reactive etching by ClF3/Ar neutral cluster beam with scanning. *Japanese Journal of Applied Physics*, **2016**, 55, 06HB01	1.4	5
252	Secondary ion emission from leucine and isoleucine under argon gas-cluster ion bombardment. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2016**, 34, 03H102	1.3	3
251	Yields and images of secondary ions from organic materials by different primary Bi ions in time-of-flight secondary ion mass spectrometry. *Rapid Communications in Mass Spectrometry*, **2016**, 30, 476-82	2.2	6
250	Peptide Fragmentation and Surface Structural Analysis by Means of ToF-SIMS Using Large Cluster Ion Sources. *Analytical Chemistry*, **2016**, 88, 3592-7	7.8	46
249	Ambient analysis of liquid materials with Wet-SIMS. *Nuclear Instruments & Methods in Physics Research B*, **2016**, 371, 189-193	1.2	6
248	Effects of molecular weight and cationization agent on the sensitivity of Bi cluster secondary ion mass spectrometry. *Rapid Communications in Mass Spectrometry*, **2016**, 30, 1722-1726	2.2	1
247	Development of ambient SIMS using mega-electron-volt-energy ion probe. *Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics*, **2016**, 34, 03H111	1.3	8
246	Solvent-free silver-nanoparticle surface-assisted laser desorption/ionization imaging mass spectrometry of the Irganox 1010 coated on polystyrene. *International Journal of Mass Spectrometry*, **2016**, 404, 1-7	1.9	8
245	Molecular dynamics simulations study of nano particle migration by cluster impact. *Surface and Coatings Technology*, **2016**, 306, 63-68	4.4	3
244	Development of Low-vacuum SIMS instruments with large cluster Ion beam. *Surface and Interface Analysis*, **2016**, 48, 1119-1121	1.5	3
243	High-aspect-ratio patterning by ClF3-Ar neutral cluster etching. *Microelectronic Engineering*, **2015**, 141, 145-149	2.5	6
242	Molecular cluster emission in sputtering of amino acids by argon gas-cluster ions. *International Journal of Mass Spectrometry*, **2015**, 383-384, 31-37	1.9	4
241	Progress and applications of cluster ion beam technology. *Current Opinion in Solid State and Materials Science*, **2015**, 19, 12-18	12	38
240	Quantitative analysis of lipids with argon gas cluster ion beam secondary ion mass spectrometry. *Surface and Interface Analysis*, **2014**, 46, 1129-1132	1.5	
239	Analysis of liquid materials in low vacuum with Wet-SIMS. *Surface and Interface Analysis*, **2014**, 46, 1133-1136	1.5	8
238	Biomaterial imaging with MeV-energy heavy ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 332, 326-329	1.2	6

237	Development of a TOF SIMS setup at the Zagreb heavy ion microbeam facility. *Nuclear Instruments & Methods in Physics Research B*, **2014**, 332, 234-237	1.2	22
236	Prolific cluster emission in sputtering of phenylalanine by argon-cluster ion bombardment. *International Journal of Mass Spectrometry*, **2014**, 360, 54-57	1.9	7
235	Cold ablation driven by localized forces in alkali halides. *Nature Communications*, **2014**, 5, 3863	17.4	33
234	Highly Accurate Lipid Analysis and Imaging Mass Spectrometry with Cluster SIMS. *Hyomen Kagaku*, **2014**, 35, 351-355		1
233	Development of organic SIMS system with Ar-GCIB and IMS-4f. *Surface and Interface Analysis*, **2014**, 46, 368-371	1.5	3
232	Lipid compounds analysis with MeV-SIMS apparatus for biological applications. *Surface and Interface Analysis*, **2014**, 46, 353-356	1.5	1
231	Development of Au-GCIB Dynamic SIMS and Cluster Size Filtering System. *Microscopy and Microanalysis*, **2014**, 20, 1152-1153	0.5	
230	Low Vacuum SIMS Measurements of Higher Alcohols with MeV-energy Heavy Ion Beam. *Transactions of the Materials Research Society of Japan*, **2014**, 39, 265-268	0.2	2
229	Mass analysis by Ar-GCIB-dynamic SIMS for organic materials. *Surface and Interface Analysis*, **2014**, 46, 1212-1214	1.5	3
228	Study on the detection limits of a new argon gas cluster ion beam secondary ion mass spectrometry apparatus using lipid compound samples. *Rapid Communications in Mass Spectrometry*, **2014**, 28, 917-20	2.2	12
227	Novel SIMS system with focused massive cluster ion source for mass imaging spectrometry with high lateral resolution. *Applied Physics Express*, **2014**, 7, 056602	2.4	32
226	Sputtered ion emission under size-selected Arn+ cluster ion bombardment. *Surface and Interface Analysis*, **2013**, 45, 138-142	1.5	19
225	Ion-induced damage evaluation with Ar cluster ion beams. *Surface and Interface Analysis*, **2013**, 45, 167-170	1.5	9
224	Development of gas cluster ion beam irradiation system with an orthogonal acceleration TOF instrument. *Surface and Interface Analysis*, **2013**, 45, 522-524	1.5	15
223	An electrostatic quadrupole doublet focusing system for MeV heavy ions in MeV-SIMS. *Nuclear Instruments & Methods in Physics Research B*, **2013**, 315, 356-359	1.2	5
222	Ultrafast Hot Electron Induced Phase Transitions in Vanadium Dioxide. *EPJ Web of Conferences*, **2013**, 41, 03005	0.3	
221	Molecular dynamics simulation study of damage formation and sputtering with huge fluorine cluster impact on silicon. *Nuclear Instruments & Methods in Physics Research B*, **2013**, 303, 170-173	1.2	3
220	Ultrafine Particle Removal Using Gas Cluster Ion Beam Technology. *IEEE Transactions on Semiconductor Manufacturing*, **2013**, 26, 328-334	2.6	4

219	Peptide dissociation patterns in secondary ion mass spectrometry under large argon cluster ion bombardment. *Rapid Communications in Mass Spectrometry*, **2013**, 27, 1490-6	2.2	16
218	Molecular dynamics study of crater formation by core-shell structured cluster impact. *Nuclear Instruments & Methods in Physics Research B*, **2012**, 282, 29-32	1.2	6
217	Hot electron injection driven phase transitions. *Physical Review B*, **2012**, 86,	3.3	27
216	Femtosecond electron diffraction: Preparation and characterization of (110)-oriented bismuth films. *Journal of Applied Physics*, **2012**, 111, 043504	2.5	19
215	Strongly reduced fragmentation and soft emission processes in sputtered ion formation from amino acid films under large Ar(n)+ (n □200) cluster ion bombardment. *Rapid Communications in Mass Spectrometry*, **2012**, 26, 1-8	2.2	41
214	Depth profiling analysis of damaged arginine films with Ar cluster ion beams. *Surface and Interface Analysis*, **2012**, 44, 729-731	1.5	5
213	Ultrafast X-ray sources for time-resolved measurements. *X-Ray Spectrometry*, **2012**, 41, 188-194	0.9	4
212	Photo-induced lattice softening of excited-state VO2. *Applied Physics Letters*, **2011**, 99, 051903	3.4	26
211	Energy effects on the sputtering yield of Si bombarded with gas cluster ion beams **2011**,		6
210	Evaluation of lattice motion in CdTe single crystal using in-air tabletop time-resolved X-ray diffractometer. *IOP Conference Series: Materials Science and Engineering*, **2011**, 24, 012010	0.4	
209	Etching of metallic materials with Cl2 gas cluster ion beam. *Surface and Coatings Technology*, **2011**, 206, 789-791	4.4	2
208	Highly sensitive molecular detection with swift heavy ions. *Nuclear Instruments & Methods in Physics Research B*, **2011**, 269, 2251-2253	1.2	18
207	MeV-energy probe SIMS imaging of major components in washed and fractured animal cells. *Surface and Interface Analysis*, **2011**, 43, 363-366	1.5	4
206	Surface morphology of PMMA surfaces bombarded with size-selected gas cluster ion beams. *Surface and Interface Analysis*, **2011**, 43, 120-122	1.5	16
205	Using ellipsometry for the evaluation of surface damage and sputtering yield in organic films with irradiation of argon cluster ion beams. *Surface and Interface Analysis*, **2011**, 43, 84-87	1.5	7
204	Comparison of MeV monomer ion and keV cluster ToF-SIMS. *Surface and Interface Analysis*, **2011**, 43, 249-252	1.5	26
203	Analysis of organic semiconductor multilayers with Ar cluster secondary ion mass spectrometry. *Surface and Interface Analysis*, **2011**, 43, 95-98	1.5	32
202	The effect of incident energy on molecular depth profiling of polymers with large Ar cluster ion beams. *Surface and Interface Analysis*, **2011**, 43, 221-224	1.5	19

201	Molecular dynamics simulations of large fluorine cluster impact on silicon with supersonic velocity. *Nuclear Instruments & Methods in Physics Research B*, **2011**, 269, 1582-1585	1.2	7
200	Characterization of vapor-deposited l-leucine nanofilm. *Thin Solid Films*, **2011**, 519, 1993-1997	2.2	1
199	Low-damage milling of an amino acid thin film with cluster ion beam. *Journal of Applied Physics*, **2011**, 110, 094701	2.5	2
198	Biomolecular Emission by Swift Heavy Ion Bombardment **2011**,		1
197	Evaluation of surface damage on organic materials irradiated with Ar cluster ion beam **2011**,		4
196	High Speed Si Etching with ClF3 Cluster Injection **2011**,		6
195	Processing Techniques of Biomaterials Using Ar Cluster Ion Beam for Imaging Mass Spectrometry. *Transactions of the Materials Research Society of Japan*, **2010**, 35, 793-796	0.2	
194	Organic depth profiling of a nanostructured delta layer reference material using large argon cluster ions. *Analytical Chemistry*, **2010**, 82, 98-105	7.8	141
193	Characterization of structural dynamics of VO2 thin film on c-Al2O3 using in-air time-resolved x-ray diffraction. *Physical Review B*, **2010**, 82,	3.3	58
192	MD simulation of small boron cluster implantation **2010**,		1
191	Evaluation of Damage Layer in an Organic Film with Irradiation of Energetic Ion Beams. *Japanese Journal of Applied Physics*, **2010**, 49, 036503	1.4	12
190	Anisotropic Etching Using Reactive Cluster Beams. *Applied Physics Express*, **2010**, 3, 126501	2.4	10
189	Effects of ambient pressure on Cu K□X-ray radiation with millijoule and high-repetition-rate femtosecond laser. *Applied Physics B: Lasers and Optics*, **2010**, 99, 173-179	1.9	13
188	MeV-energy probe SIMS imaging of major components in animal cells etched using large gas cluster ions. *Nuclear Instruments & Methods in Physics Research B*, **2010**, 268, 1736-1740	1.2	17
187	Molecular dynamics simulations for gas cluster ion beam processes. *Vacuum*, **2010**, 84, 994-998	3.7	35
186	SIMS with highly excited primary beams for molecular depth profiling and imaging of organic and biological materials. *Surface and Interface Analysis*, **2010**, 42, 1612-1615	1.5	31
185	Recent Progress in Cluster Ion Beam Technology. *Hyomen Kagaku*, **2010**, 31, 564-571		3
184	Development of Ultrafast Pulse X-ray Source in Ambient Pressure with a Millijoule High Repetition Rate Femtosecond Laser. *Green Energy and Technology*, **2010**, 300-305	0.6	

183	Sputtering yield measurements with size-selected gas cluster ion beams. *Materials Research Society Symposia Proceedings*, **2009**, 1181, 150		4
182	Matrix-free high-resolution imaging mass spectrometry with high-energy ion projectiles. *Journal of Mass Spectrometry*, **2009**, 44, 128-36	2.2	44
181	High-speed processing with Cl2 cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 1444-1446	1.2	6
180	The emission process of secondary ions from solids bombarded with large gas cluster ions. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 2601-2604	1.2	10
179	Precise and fast secondary ion mass spectrometry depth profiling of polymer materials with large Ar cluster ion beams. *Rapid Communications in Mass Spectrometry*, **2009**, 23, 1601-6	2.2	174
178	Molecular depth profiling of multilayer structures of organic semiconductor materials by secondary ion mass spectrometry with large argon cluster ion beams. *Rapid Communications in Mass Spectrometry*, **2009**, 23, 3264-8	2.2	86
177	Study of crater formation and sputtering process with large gas cluster impact by molecular dynamics simulations. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 1424-1427	1.2	10
176	Imaging mass spectrometry with nuclear microprobes for biological applications. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 2144-2148	1.2	12
175	Study of density effect of large gas cluster impact by molecular dynamics simulations. *Nuclear Instruments & Methods in Physics Research B*, **2009**, 267, 2999-3001	1.2	11
174	Development of femtosecond X-ray source in helium atmosphere with millijoule high-repetition-rate femtosecond laser. *Transactions of the Materials Research Society of Japan*, **2009**, 34, 621-626	0.2	3
173	Carbon Nanotubes from a Divided Catalyst: the Carbon Transmission Method. *Applied Physics Express*, **2008**, 1, 034002	2.4	4
172	A fragment-free ionization technique for organic mass spectrometry with large Ar cluster ions. *Applied Surface Science*, **2008**, 255, 1588-1590	6.7	54
171	MD simulation study of the sputtering process by high-energy gas cluster impact. *Applied Surface Science*, **2008**, 255, 944-947	6.7	11
170	Secondary ion emission from Si bombarded with large Ar cluster ions under UHV conditions. *Applied Surface Science*, **2008**, 255, 880-882	6.7	7
169	High sputtering yields of organic compounds by large gas cluster ions. *Applied Surface Science*, **2008** , 255, 1148-1150	6.7	51
168	What size of cluster is most appropriate for SIMS?. *Applied Surface Science*, **2008**, 255, 1235-1238	6.7	41
167	Yield enhancement of molecular ions with MeV ion-induced electronic excitation. *Applied Surface Science*, **2008**, 255, 1591-1594	6.7	18
166	Recent Progress in Cluster Ion Beam. *Journal of Surface Analysis (Online)*, **2008**, 14, 196-203	0.1	5

165	Low Damage Etching and SIMS Depth Profiling with Large Ar Cluster Ions. *Transactions of the Materials Research Society of Japan*, **2008**, 33, 1043-1046	0.2	1
164	High-Speed Nanoprocessing with Cluster Ion Beams. *Transactions of the Materials Research Society of Japan*, **2008**, 33, 1019-1022	0.2	
163	Surface processing with high-energy gas cluster ion beams. *Surface and Coatings Technology*, **2007**, 201, 8646-8649	4.4	5
162	Low damage smoothing of magnetic materials using off-normal gas cluster ion beam irradiation. *Surface and Coatings Technology*, **2007**, 201, 8632-8636	4.4	6
161	Molecular dynamics study of monomer and dimer emission processes with high energy gas cluster ion impact. *Surface and Coatings Technology*, **2007**, 201, 8427-8430	4.4	5
160	Molecular dynamics study of surface modification with a glancing angle gas cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 255, 265-268	1.2	12
159	Surface oxidation of Si assisted by irradiation with large gas cluster ion beam in an oxygen atmosphere. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 256, 350-353	1.2	5
158	Molecular dynamics simulations of surface smoothing and sputtering process with glancing-angle gas cluster ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 645-648	1.2	14
157	Effect of oblique irradiation of gas cluster ion beam on surface properties of gold mirrors. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 649-652	1.2	2
156	High-speed processing with high-energy SF6 cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 666-669	1.2	11
155	Low damage smoothing of magnetic material films using a gas cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 677-682	1.2	17
154	Low-damage surface smoothing of laser crystallized polycrystalline silicon using gas cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 658-661	1.2	7
153	Molecular dynamics study of glancing angle gas cluster irradiation on irregular-structured surfaces. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 261, 639-642	1.2	16
152	Measurements of secondary ions emitted from organic compounds bombarded with large gas cluster ions. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 256, 493-496	1.2	140
151	Secondary ion emission from bio-molecular thin films under ion bombardment. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 256, 489-492	1.2	12
150	The effect of incident cluster ion energy and size on secondary ion yields emitted from Si. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 256, 528-531	1.2	25
149	Size effect in cluster collision on solid surfaces. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 257, 627-631	1.2	21
148	Energy distribution of high-energy cluster ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2007**, 261, 647-650	1.2	8

147	Cluster Ion Implantation - Prospects and Challenges- **2007**,		1
146	High-Speed Nano-Processing with Cluster Ion Beams. *AIP Conference Proceedings*, **2006**,	0	2
145	Cluster size dependence of sputtering yield by cluster ion beam irradiation. *Nuclear Instruments & Methods in Physics Research B*, **2006**, 242, 179-181	1.2	52
144	ITO surface smoothing with argon cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2006**, 242, 140-142	1.2	9
143	Molecular dynamics simulations of surface modification and damage formation by gas cluster ion impacts. *Nuclear Instruments & Methods in Physics Research B*, **2006**, 242, 517-519	1.2	27
142	High-intensity Si cluster ion emission from a silicon target bombarded with large Ar cluster ions. *Applied Surface Science*, **2006**, 252, 6550-6553	6.7	7
141	Secondary ion measurements for oxygen cluster ion SIMS. *Applied Surface Science*, **2006**, 252, 7290-7292	6.7	5
140	Molecular dynamics study of particle emission by reactive cluster ion impact. *Applied Surface Science*, **2006**, 252, 6466-6469	6.7	5
139	COMPARISON OF IRRADIATION EFFECTS BETWEEN CLUSTER AND MONOMER FOR DLC FILM DEPOSITION **2005**, 245-248		
138	Molecular dynamics simulations of sequential cluster ion impacts. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 228, 46-50	1.2	20
137	Sidewall polishing with a gas cluster ion beam for photonic device applications. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 241, 622-625	1.2	19
136	Total sputtering yields of solids under MeV-energy Si ion bombardment. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 230, 483-488	1.2	2
135	Secondary neutral and ionized particle measurements under MeV-energy ion bombardment. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 230, 489-494	1.2	1
134	Development of 1 mA cluster ion beam source. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 237, 455-458	1.2	9
133	Molecular dynamics study of the angular dependence of reactive cluster impacts. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 241, 594-598	1.2	3
132	Energy distributions of high current cluster ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2005**, 241, 604-608	1.2	6
131	Size and energy distribution of gas cluster ion beam measured by energy resolved time of flight mass spectroscopy. *Surface and Coatings Technology*, **2005**, 196, 198-202	4.4	3
130	DEVELOPMENT OF THE LARGE CURRENT CLUSTER ION BEAM TECHNOLOGY **2005**, 223-226		

129	Molecular Dynamics Simulations of the Cluster-size Effect on Sputtering Process with Reactive Gas Cluster Ions. *Materials Research Society Symposia Proceedings*, **2005**, 908, 1		
128	SURFACE STRUCTURE DEPENDENCE OF IMPACT PROCESSES OF GAS CLUSTER IONS **2005**, 231-234		
127	GAS CLUSTER ION BEAM SOURCE FOR SECONDARY ION EMISSION MEASUREMENTS **2005**, 227-230		
126	Polishing of Sidewall Surfaces Using a Gas Cluster Ion Beam. *Japanese Journal of Applied Physics*, **2004**, 43, L1253-L1255	1.4	14
125	High-speed Processing with Reactive Cluster Ion Beams. *Materials Research Society Symposia Proceedings*, **2004**, 843, 3361		4
124	Low Damage Smoothing of Magnetic Materials using Oblique Irradiation of Gas Cluster Ion Beam. *Materials Research Society Symposia Proceedings*, **2004**, 843, 551		5
123	Molecular Dynamics Study of Suface Structure and Sputtering Process by Sequencial Fluorine Cluster Impacts. *Materials Research Society Symposia Proceedings*, **2004**, 843, 571		4
122	Surface modification with gas cluster ion beams from fundamental characteristics to applications. *Nuclear Instruments & Methods in Physics Research B*, **2004**, 216, 379-389	1.2	29
121	Surface structure dependence of impact processes of gas cluster ions. *Nuclear Instruments & Methods in Physics Research B*, **2004**, 216, 185-190	1.2	16
120	Surface smoothing with large current cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2004**, 216, 191-195	1.2	18
119	A new secondary ion mass spectrometry (SIMS) system with high-intensity cluster ion source. *Nuclear Instruments & Methods in Physics Research B*, **2004**, 219-220, 463-467	1.2	55
118	High Current Cluster Ion Beam Source. *AIP Conference Proceedings*, **2003**,	0	2
117	Fast Neutral Ar Penetration during Gas Cluster Ion Beam Irradiation into Magnetic Thin Films. *Materials Research Society Symposia Proceedings*, **2003**, 792, 609		
116	Hard DLC film formation by gas cluster ion beam assisted deposition. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 201, 405-412	1.2	36
115	Molecular dynamics study of damage formation characteristics by large cluster ion impacts. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 202, 278-282	1.2	49
114	Cluster ion beam process technology. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 820-829	1.2	43
113	Atomistic study of cluster collision on solid surfaces. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 838-841	1.2	8
112	Modeling of surface smoothing process by cluster ion beam irradiation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 842-845	1.2	9

111	Gold nanoparticles sputtered by single ions and clusters. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 851-854	1.2	12
110	Defect characteristics by boron cluster ion implantation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 855-860	1.2	13
109	Cluster species and cluster size dependence of damage formation by cluster ion impact. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 861-865	1.2	12
108	Titanium-dioxide film formation using gas cluster ion beam assisted deposition technique. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 866-869	1.2	4
107	Influence of residual Ar+ in Ar cluster ion beam for DLC film formation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 884-888	1.2	2
106	Generation of the large current cluster ion beam. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 206, 902-906	1.2	67
105	Molecular effect on projected range in ultralow-energy ion implantation. *Nuclear Instruments & Methods in Physics Research B*, **2003**, 211, 206-210	1.2	9
104	Secondary ion mass spectrometry with gas cluster ion beams. *Applied Surface Science*, **2003**, 203-204, 214-218	6.7	30
103	Molecular Dynamics Study Of Surface Morphological Evolution By Cluster Impacts. *Materials Research Society Symposia Proceedings*, **2003**, 792, 383		
102	High-speed Processing with Cluster Ion Beams. *Materials Research Society Symposia Proceedings*, **2003**, 792, 580		2
101	Secondary ion mass spectrometry with gas cluster ion beams. *Nuclear Instruments & Methods in Physics Research B*, **2002**, 190, 860-864	1.2	37
100	High quality ITO film formation by the simultaneous use of cluster ion beam and laser irradiation. *Materials Chemistry and Physics*, **2002**, 74, 104-108	4.4	18
99	Scanning tunneling microscope observations of Ge deposition on Si(111)-7□ surfaces irradiated by Xe ions. *Thin Solid Films*, **2002**, 405, 141-145	2.2	5
98	Threshold Energy for Generating Damage with Cluster Ion Irradiation. *Materials Research Society Symposia Proceedings*, **2002**, 749, 1		
97	Study of Surface Morphological Evolution by Cluster Ion Irradiation on Solid Targets. *Materials Research Society Symposia Proceedings*, **2002**, 749, 1		
96	Materials processing by gas cluster ion beams. *Materials Science and Engineering Reports*, **2001**, 34, 231-295	359	359
95	Craters produced on Al, Cu and Au by Ar cluster impacts. *Nuclear Instruments & Methods in Physics Research B*, **2001**, 175-177, 36-39	1.2	7
94	Cluster size effect on reactive sputtering by fluorine cluster impact using molecular dynamics simulation. *Nuclear Instruments & Methods in Physics Research B*, **2001**, 180, 164-170	1.2	9

93	Molecular dynamics and Monte-Carlo simulation of sputtering and mixing by ion irradiation. *Nuclear Instruments & Methods in Physics Research B*, **2001**, 180, 312-316	1.2	24
92	Molecular dynamics simulation of fluorine ion etching of silicon. *Nuclear Instruments & Methods in Physics Research B*, **2001**, 180, 317-321	1.2	10
91	Modification of polycarbonate and polypropylene surfaces by argon ion cluster beams. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2001**, 19, 2050		15
90	Characterization of Damage Induced by Cluster Ion Implantation. *Materials Research Society Symposia Proceedings*, **2001**, 669, 1		3
89	Photoluminescence study of defects induced by B10H14 ions. *Materials Research Society Symposia Proceedings*, **2001**, 669, 1		
88	Secondary Ion Mass Spectrometry with Gas Cluster Ion Beams. *Materials Research Society Symposia Proceedings*, **2000**, 647, 1		
87	Ar Cluster Ion Bombardment Effects on Semiconductor Surfaces. *Materials Research Society Symposia Proceedings*, **2000**, 647, 1		1
86	Molecular Dynamics Simulations of Cluster Ion Impact on Diamond Surface. *Materials Research Society Symposia Proceedings*, **2000**, 650, 3401		5
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3	Cluster ion implantation for shallow junction formation	6
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